4V Drive Pch MOSFET

AEC-Q101 Qualified

RSL020P03FRA

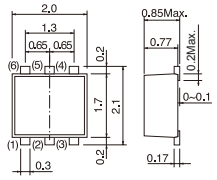
●Structure
Silicon P-channel MOSFET

●Features
1) Low On-resistance.
2) High speed switching.

●Applications
Switching

●Dimensions (Unit : mm)

TUMT6

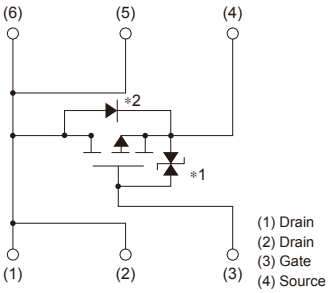


Abbreviated symbol : SL

●Packaging specifications

Type	Package	Taping
	Code	TR
	Quantity (pcs)	3000
RSL020P03FRA		○

●Inner circuit



*1 ESD PROTECTION DIODE
*2 BODY DIODE

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±2	A
	Pulsed	I_{DP} *1	±8	A
Source current (Body diode)	Continuous	I_S	−0.8	A
	Pulsed	I_{SP} *1	−8	A
Total power dissipation		P_D *2	1	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	125	°C/W

* Mounted on a ceramic board

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}= ±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	–30	–	–	V	I_D= –1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}= –30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–1.0	–	–2.5	V	V_{DS}= –10V, I_D= –1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	80	120	mΩ	I_D= –2A, V_{GS}= –10V
		–	125	190	mΩ	I_D=–1A, V_{GS}= –4.5V
		–	140	210	mΩ	I_D= –1A, V_{GS}= –4.0V
Forward transfer admittance	$\|Y_{fs}\|$ *	1.4	–	–	S	V_{DS}= –10V, I_D= –1A
Input capacitance	C_{iss}	–	350	–	pF	V_{DS}= –10V
Output capacitance	C_{oss}	–	80	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	50	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	11	–	ns	V_{DD}≒ –15V I_D= –1A V_{GS}= –10V R_L=15Ω R_G =10Ω
Rise time	t_r *	–	11	–	ns	
Turn-off delay time	$t_{d\ (off)}$ *	–	35	–	ns	
Fall time	t_f *	–	11	–	ns	
Total gate charge	Q_g	–	3.9	–	nC	V_{DD}≒ –15V V_{GS}= –5V
Gate-source charge	Q_{gs}	–	1.3	–	nC	I_D= –2A
Gate-drain charge	Q_{gd}	–	1.1	–	nC	R_L=7.5Ω R_G =10Ω

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	I_S= –0.8A, V_{GS}=0V

●Electrical characteristics curves

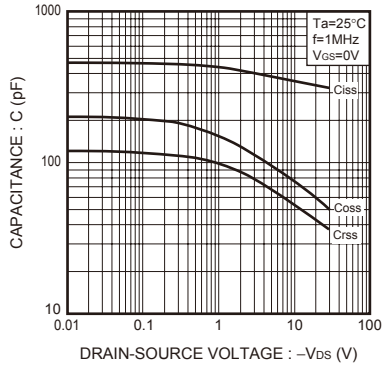


Fig.1 Typical Capacitance vs. Drain-Source Voltage

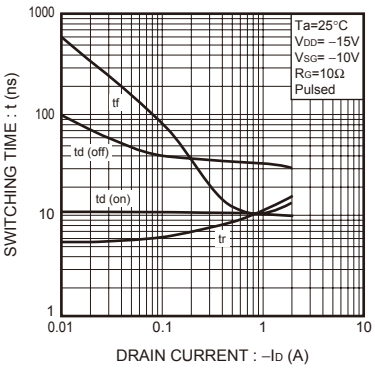


Fig.2 Switching Characteristics

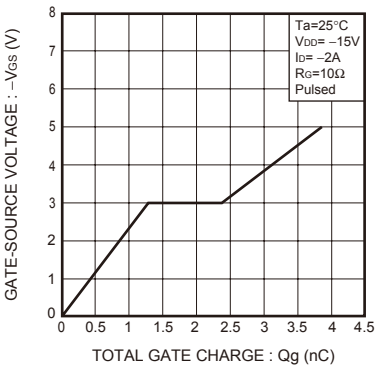


Fig.3 Dynamic Input Characteristics

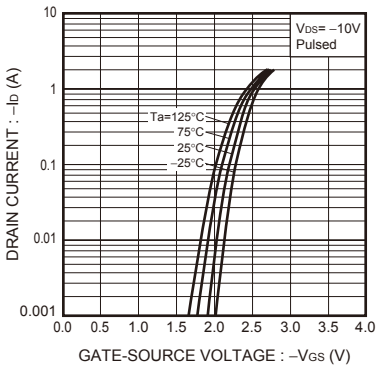


Fig.4 Typical Transfer Characteristics

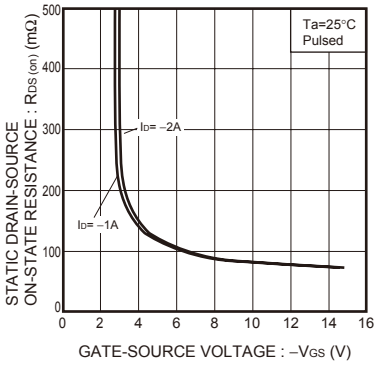


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

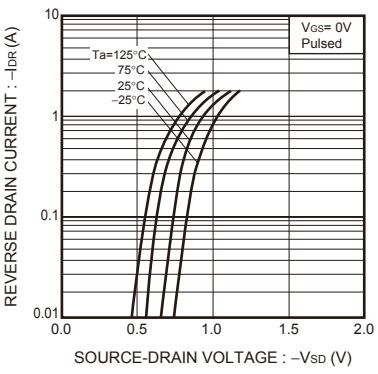


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

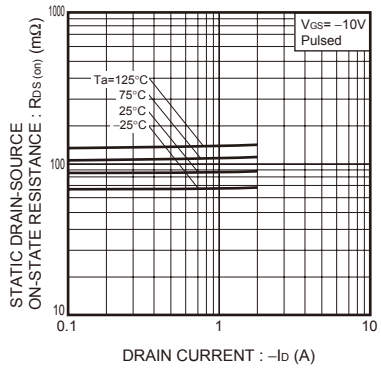


Fig.7 Static Drain-Source On-State Resistance vs. Drain current (I)

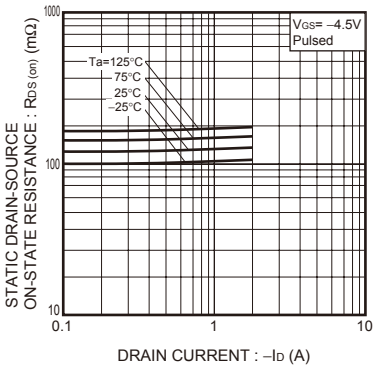


Fig.8 Static Drain-Source On-State Resistance vs. Drain current (II)

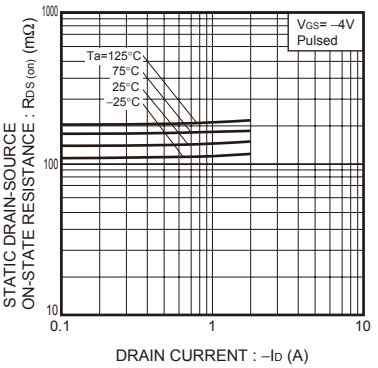


Fig.9 Static Drain-Source On-State Resistance vs. Drain current (III)

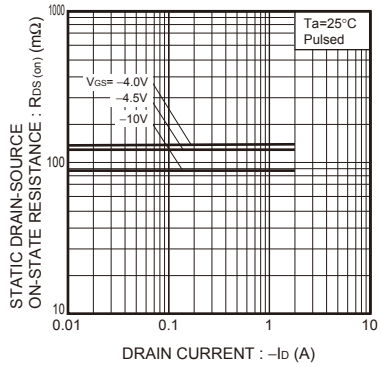


Fig.10 Static Drain-Source On-State Resistance vs. Drain current (Ⅳ)

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BA50BC0FP-E2 EDZVT2R6.8B DTB113EKT146 SH8M24TB1 BD6290EFV-E2 BD750L2EFJ-CE2
BR24G02FJ-3GTE2 BU4825G-TR ESR10EZPF2000 RB168M150TR SST2222AT116 BM2P134E-EVK-001
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